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List of Publications by Year
in descending order

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444	6,195	117625	155660
papers	citations	34 h-index	55 g-index

445	445	445	2404
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	On the flicker noise in submicron silicon MOSFETs. Solid-State Electronics, 1999, 43, 865-882.	1.4	303
2	Low-frequency noise behavior of SiO/sub 2/--HfO/sub 2/ dual-layer gate dielectric nMOSFETs with different interfacial oxide thickness. IEEE Transactions on Electron Devices, 2004, 51, 780-784.	3.0	136
3	A theoretical study of the critical radius of precipitates and its application to silicon oxide in silicon. Journal of Applied Physics, 1987, 62, 3960-3967.	2.5	127
4	"Linear kink effect" induced by electron valence band tunneling in ultrathin gate oxide bulk and SOI MOSFETs. IEEE Transactions on Electron Devices, 2003, 50, 1675-1682.	3.0	113
5	$1/f$ Noise in Drain and Gate Current of MOSFETs With High-k Gate Stacks. IEEE Transactions on Device and Materials Reliability, 2009, 9, 180-189.	2.0	107
6	The low-frequency noise behaviour of silicon-on-insulator technologies. Solid-State Electronics, 1996, 39, 949-960.	1.4	97
7	Low-frequency noise in silicon-on-insulator devices and technologies. Solid-State Electronics, 2007, 51, 16-37.	1.4	94
8	Gettering mechanisms in silicon. Journal of Applied Physics, 1988, 64, 869-876.	2.5	85
9	Impact of oxygen related extended defects on silicon diode characteristics. Journal of Applied Physics, 1995, 77, 5669-5676.	2.5	74
10	D.c. and low frequency noise characteristics of Î³-irradiated gate-all-around silicon-on-insulator MOS transistors. Solid-State Electronics, 1995, 38, 1-8.	1.4	73
11	Filmâ€edgeâ€induced dislocation generation in silicon substrates. I. Theoretical model. Journal of Applied Physics, 1987, 61, 2170-2175.	2.5	72
12	Challenges and opportunities in advanced Ge pMOSFETs. Materials Science in Semiconductor Processing, 2012, 15, 588-600.	4.0	72
13	Model for hysteresis and kink behavior of MOS transistors operating at 4.2 K. IEEE Transactions on Electron Devices, 1988, 35, 1120-1125.	3.0	70
14	Impact strain engineering on gate stack quality and reliability. Solid-State Electronics, 2008, 52, 1115-1126.	1.4	69
15	Impact of Donor Concentration, Electric Field, and Temperature Effects on the Leakage Current in Germanium p $+/$n Junctions. IEEE Transactions on Electron Devices, 2008, 55, 2287-2296.	3.0	69
16	Short-channel radiation effect in 60 MeV proton irradiated 0.13Î¼m CMOS transistors. IEEE Transactions on Nuclear Science, 2003, 50, 2426-2432.	2.0	61
17	Random Telegraph Signal: a local probe for single point defect studies in solid-state devices. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 136-143.	3.5	59
18	Laser- and Heavy Ion-Induced Charge Collection in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2011, 58, 2563-2569.	2.0	58

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19	Impact of the interfacial layer on the low-frequency noise (1/f) behavior of MOSFETs with advanced gate stacks. IEEE Electron Device Letters, 2006, 27, 688-691.	3.9	54
20	Geometry Dependence of Total-Dose Effects in Bulk FinFETs. IEEE Transactions on Nuclear Science, 2014, 61, 2951-2958.	2.0	54
21	On the Temperature and Field Dependence of Trap-Assisted Tunneling Current in Ge $hbox{p}^{+}hbox{n}$ Junctions. IEEE Electron Device Letters, 2009, 30, 562-564.	3.9	49
22	Impact of Fe and Cu Contamination on the Minority Carrier Lifetime of Silicon Substrates. Journal of the Electrochemical Society, 1996, 143, 3014-3019.	2.9	48
23	Filmâ€edgeâ€induced dislocation generation in silicon substrates. II. Application of the theoretical model for local oxidation processes on (001) silicon substrates. Journal of Applied Physics, 1987, 61, 2176-2188.	2.5	46
24	Impact of silicidation on the excess noise behaviour of mos transistors. Solid-State Electronics, 1995, 38, 1893-1897.	1.4	46
25	Freeze-out effects on NMOS transistor characteristics at 4.2 K. IEEE Transactions on Electron Devices, 1989, 36, 1155-1161.	3.0	45
26	Low temperature noise spectroscopy of 0.1â€‰Î¼m partially depleted silicon on insulator metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2007, 101, 104511.	2.5	45
27	Extraction of the minority carrier recombination lifetime from forward diode characteristics. Applied Physics Letters, 1995, 66, 2894-2896.	3.3	41
28	The behavior of silicon p-n junction-based devices at liquid helium temperatures. Journal of Applied Physics, 1991, 70, 1016-1024.	2.5	40
29	Activation energy analysis as a tool for extraction and investigation of pâ€“n junction leakage current components. Journal of Applied Physics, 2003, 94, 1218-1221.	2.5	39
30	Correlation between the 1â•f noise parameters and the effective low-field mobility in HfO2 gate dielectric n-channel metalâ€“oxideâ€“semiconductor field-effect transistors. Applied Physics Letters, 2004, 85, 1057-1059.	3.3	39
31	Electron valence-band tunneling-induced Lorentzian noise in deep submicron silicon-on-insulator metalâ€“oxideâ€“semiconductor field-effect transistors. Journal of Applied Physics, 2003, 94, 4461-4469.	2.5	37
32	Critical Discussion of the Frontâ€“Back Gate Coupling Effect on the Low-Frequency Noise in Fully Depleted SOI MOSFETs. IEEE Transactions on Electron Devices, 2004, 51, 1008-1016.	3.0	36
33	Impact of high-k gate stack material with metal gates on LF noise in n- and p-MOSFETs. Microelectronic Engineering, 2005, 80, 226-229.	2.4	36
34	Low-Frequency Noise Performance of HfO[sub 2]-Based Gate Stacks. Journal of the Electrochemical Society, 2005, 152, F115.	2.9	36
35	Processing aspects in the low-frequency noise of nMOSFETs on strained-silicon substrates. IEEE Transactions on Electron Devices, 2006, 53, 1039-1047.	3.0	35
36	Low-Frequency Noise Assessment of Silicon Passivated Ge pMOSFETs With TiN/TaN/ $hbox{HfO}_{2}$ Gate Stack. IEEE Electron Device Letters, 2007, 28, 288-291.	3.9	35

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37	Low-frequency noise overshoot in ultrathin gate oxide silicon-on-insulator metalâ€“oxideâ€“semiconductor field-effect transistors. Applied Physics Letters, 2003, 82, 1790-1792.	3.3	34
38	Effective generationâ€“recombination parameters in highâ€energy proton irradiated silicon diodes. Applied Physics Letters, 1996, 69, 2858-2860.	3.3	33
39	Optimized Diode Analysis of Electrical Silicon Substrate Properties. Journal of the Electrochemical Society, 1998, 145, 2107-2112.	2.9	33
40	Tunneling 1/fÎ³ noise in 5nm HfO2/2.1nm SiO2 gate stack n-MOSFETs. Solid-State Electronics, 2005, 49, 702-707.	1.4	33
41	The charge transport in a silicon resistor at liquidâ€helium temperatures. Journal of Applied Physics, 1990, 68, 4091-4099.	2.5	32
42	Impact of the substrate on the lowâ€frequency noise of silicon n+p junction diodes. Applied Physics Letters, 1995, 66, 2507-2509.	3.3	32
43	Noise as a Diagnostic Tool for Semiconductor Material and Device Characterization. Journal of the Electrochemical Society, 1998, 145, 2058-2067.	2.9	32
44	Low-Frequency Noise Assessment for Deep Submicrometer CMOS Technology Nodes. Journal of the Electrochemical Society, 2004, 151, G307.	2.9	32
45	Evaluation of triple-gate FinFETs with SiO2â€“HfO2â€“TiN gate stack under analog operation. Solid-State Electronics, 2007, 51, 285-291.	1.4	32
46	Study of ohmic contacts to n-type Ge: Snowplow and laser activation. Applied Physics Letters, 2011, 99, .	3.3	32
47	Tin Doping of Silicon for Controlling Oxygen Precipitation and Radiation Hardness. Journal of the Electrochemical Society, 2001, 148, G738.	2.9	30
48	Influence of the substrate voltage on the random telegraph signal parameters in submicron n -channel metal-oxide-semiconductor field-effect transistors under a constant inversion charge density. Applied Physics A: Materials Science and Processing, 2000, 70, 345-353.	2.3	29
49	Geometry and Strain Dependence of the Proton Radiation Behavior of MuGFET Devices. IEEE Transactions on Nuclear Science, 2007, 54, 2227-2232.	2.0	29
50	Oxide phase determination in silicon using infrared spectroscopy and transmission electron microscopy techniques. Journal of Applied Physics, 2002, 91, 2493-2498.	2.5	28
51	Low-frequency noise assessment in advanced UTBOX SOI nMOSFETs with different gate dielectrics. Solid-State Electronics, 2014, 97, 14-22.	1.4	28
52	Analytical model for the kink in nMOSTs operating at Liquid Helium Temperatures (LHT). Solid-State Electronics, 1990, 33, 445-454.	1.4	27
53	Excess carrier cross-sectional profiling technique for determination of the surface recombination velocity. Materials Science in Semiconductor Processing, 2001, 4, 125-131.	4.0	27
54	Substrate orientation, doping and plasma frequency dependencies of structural defect formation in hydrogen plasma treated silicon. Journal of Physics Condensed Matter, 2002, 14, 13037-13045.	1.8	27

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55	Low-frequency (1/f) noise behavior of locally stressed HfO/sub 2//TiN gate-stack pMOSFETs. IEEE Electron Device Letters, 2006, 27, 508-510.	3.9	27
56	Gate electrode effects on low-frequency (1/f) noise in p-MOSFETs with high-Î¤ dielectrics. Solid-State Electronics, 2006, 50, 992-998.	1.4	27
57	Low frequency noise characterization in n-channel FinFETs. Solid-State Electronics, 2012, 70, 20-26.	1.4	27
58	Sensitive Light Scattering as a Semiquantitative Method for Studying Photoresist Stripping. Journal of the Electrochemical Society, 1995, 142, 211-216.	2.9	26
59	Accurate extraction of the diffusion current in silicon p-n junction diodes. Applied Physics Letters, 1998, 72, 1054-1056.	3.3	26
60	Influence of Fin Width on the Total Dose Behavior of p-Channel Bulk MuGFETs. IEEE Electron Device Letters, 2010, 31, 243-245.	3.9	26
61	Hot-Carrier degradation of the Random Telegraph Signal amplitude in submicrometer Si MOSTs. Applied Physics A: Solids and Surfaces, 1993, 57, 283-289.	1.4	25
62	Integration of CMOS-electronics and particle detector diodes in high-resistivity silicon-on-insulator wafers. IEEE Transactions on Nuclear Science, 1993, 40, 753-758.	2.0	25
63	Development of silicon micropattern pixel detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1994, 348, 399-408.	1.6	25
64	Analytical model for the 1âˆ•f noise in the tunneling current through metal-oxide-semiconductor structures. Journal of Applied Physics, 2009, 106, .	2.5	25
65	What Do We Know about Hydrogen-Induced Thermal Donors in Silicon?. Journal of the Electrochemical Society, 2009, 156, H434.	2.9	25
66	Evidence of different conduction mechanisms in accumulation-mode p-channel SOI MOSFET's at room and liquid-helium temperatures. IEEE Transactions on Electron Devices, 1993, 40, 727-732.	3.0	24
67	Back and front interface related generation-recombination noise in buried-channel SOI pMOSFETs. IEEE Transactions on Electron Devices, 1996, 43, 417-423.	3.0	24
68	Total ionizing dose damage in deep submicron partially depleted SOI MOSFETs induced by proton irradiation. Solid-State Electronics, 2004, 48, 1045-1054.	1.4	24
69	Strained Si/SiGe MOS technology: Improving gate dielectric integrity. Microelectronic Engineering, 2009, 86, 218-223.	2.4	24
70	The Perspectives of Siliconâ€onâ€Insulator Technologies for Cryogenic Applications. Journal of the Electrochemical Society, 1994, 141, 2522-2532.	2.9	22
71	On the gate- and drain-voltage dependence of the RTS amplitude in submicron MOSTs. Applied Physics A: Solids and Surfaces, 1994, 58, 353-358.	1.4	22
72	On the impact of low fluence irradiation with MeV particles on silicon diode characteristics and related material properties. IEEE Transactions on Nuclear Science, 1994, 41, 1924-1931.	2.0	22

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73	Non-trivial GR and 1/fnoise generated in the p-Si layer of SOI and SOS MOSFETs near the inverted front or buried p-Si/SiO2interface. Semiconductor Science and Technology, 1999, 14, 775-783.	2.0	22
74	Deep levels in high-energy proton-irradiated tin-doped n-type Czochralski silicon. Applied Physics Letters, 2000, 76, 2838-2840.	3.3	22
75	Hydrogen plasma-enhanced thermal donor formation in n-type oxygen-doped high-resistivity float-zone silicon. Applied Physics Letters, 2002, 81, 1842-1844.	3.3	22
76	Study of metal-related deep-level defects in germanide Schottky barriers on n-type germanium. Journal of Applied Physics, 2008, 104, .	2.5	22
77	Two- and three-dimensional calculation of substrate resistance. IEEE Transactions on Electron Devices, 1988, 35, 339-352.	3.0	21
78	The importance of the internal bulk-source potential on the low temperature kink in NMOSTs. IEEE Transactions on Electron Devices, 1991, 38, 1459-1466.	3.0	21
79	A low-frequency noise study of gate-all-around SOI transistors. IEEE Transactions on Electron Devices, 1993, 40, 2054-2059.	3.0	21
80	Impact of high energy particles on InGaP/InGaAs pseudomorphic HEMTs. IEEE Transactions on Nuclear Science, 1998, 45, 2861-2866.	2.0	21
81	Reliability aspects of the low-frequency noise behaviour of submicron CMOS technologies. Semiconductor Science and Technology, 1999, 14, R61-R71.	2.0	21
82	Impact of 7.5-MeV proton irradiation on front-back gate coupling effect in ultra thin gate oxide FD-SOI n-MOSFETs. IEEE Transactions on Nuclear Science, 2004, 51, 3795-3800.	2.0	21
83	Low-Frequency (1â^•f) Noise Performance of n- and p-MOSFETs with Poly-Siâ^•Hf-Based Gate Dielectrics. Journal of the Electrochemical Society, 2006, 153, G324.	2.9	21
84	Deep level transient spectroscopy study of nickel-germanide Schottky barriers on n-type germanium. Applied Physics Letters, 2006, 88, 183506.	3.3	21
85	Impact of strain and source/drain engineering on the low frequency noise behaviour in n-channel tri-gate FinFETs. Solid-State Electronics, 2008, 52, 1889-1894.	1.4	21
86	Cryogenic operation of FinFETs aiming at analog applications. Cryogenics, 2009, 49, 590-594.	1.7	21
87	High Doping Density/High Electric Field, Stress and Heterojunction Effects on the Characteristics of CMOS Compatible p-n Junctions. Journal of the Electrochemical Society, 2011, 158, R27.	2.9	21
88	A Quantitative Model for Silicon Yield Stress Calculations at Thin Film Edges. Journal of the Electrochemical Society, 1988, 135, 1509-1517.	2.9	20
89	Anomalous kink-related excess noise in MOSFETs at 4.2 K. IEEE Transactions on Electron Devices, 1991, 38, 907-912.	3.0	20
90	Bulk defect induced low-frequency noise in n/sup +/-p silicon diodes. IEEE Transactions on Electron Devices, 1998, 45, 2528-2536.	3.0	20

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91	On the impact of the capture rates on the generation/recombination lifetime ratio of a single deep level. IEEE Transactions on Electron Devices, 1999, 46, 1487-1488.	3.0	20
92	Origin of the front-back-gate coupling in partially depleted and fully depleted silicon-on-insulator metal-oxide-semiconductor field-effect transistors with accumulated back gate. Journal of Applied Physics, 2005, 98, 114506.	2.5	20
93	On the beneficial impact of tensile-strained silicon substrates on the low-frequency noise of n-channel metal-oxide-semiconductor transistors. Applied Physics Letters, 2005, 86, 223509.	3.3	20
94	The temperature mobility degradation influence on the zero temperature coefficient of partially and fully depleted SOI MOSFETs. Microelectronics Journal, 2006, 37, 952-957.	2.0	20
95	Generation and annealing behaviour of MeV proton and /sup 252/Cf irradiation induced deep levels in silicon diodes. IEEE Transactions on Nuclear Science, 1994, 41, 479-486.	2.0	19
96	The 1/f/sup 1.7/ noise in submicron SOI MOSFETs with 2.5 nm nitrided gate oxide. IEEE Transactions on Electron Devices, 2002, 49, 2367-2370.	3.0	19
97	On the Low-Frequency Noise of pMOSFETs With Embedded SiGe Source/Drain and Fully Silicided Metal Gate. IEEE Electron Device Letters, 2007, 28, 987-989.	3.9	19
98	Si versus Ge for future microelectronics. Thin Solid Films, 2010, 518, 2301-2306.	1.8	19
99	Low-Frequency Noise Characterization of Strained Germanium pMOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 3132-3139.	3.0	19
100	(Invited) Status and Trends in Ge CMOS Technology. ECS Transactions, 2013, 54, 25-37.	0.5	19
101	The hysteresis and transient behavior of Si metalâ€oxideâ€semiconductor transistors at 4.2 K. I. The kinkâ€related counterclockwise hysteresis regime. Journal of Applied Physics, 1993, 73, 3068-3073.	2.5	18
102	1/f noise performance of MOSFETs with HfO2 and metal gate on Ge-on-insulator substrates. Materials Science in Semiconductor Processing, 2006, 9, 721-726.	4.0	18
103	Defect assessment and leakage control in Ge junctions. Microelectronic Engineering, 2014, 125, 33-37.	2.4	18
104	Reviewâ€"Device Assessment of Electrically Active Defects in High-Mobility Materials. ECS Journal of Solid State Science and Technology, 2016, 5, P3149-P3165.	1.8	18
105	Transient response of silicon devices at 4.2 K. II. Application to the case of a metal-oxide-semiconductor transistor. Semiconductor Science and Technology, 1991, 6, 905-911.	2.0	17
106	Static and low-frequency noise characteristics of n+p junction diodes fabricated in different silicon substrates. Semiconductor Science and Technology, 1995, 10, 1002-1008.	2.0	17
107	Explaining the parameters of the electron valence-band tunneling related Lorentzian noise in fully depleted SOI MOSFETs. IEEE Electron Device Letters, 2003, 24, 751-754.	3.9	17
108	Paramagnetic point defects at interfacial layers in biaxial tensile strained (100)Si/SiO2. Journal of Applied Physics, 2008, 103, .	2.5	17

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109	Analysis of the Temperature Dependence of Trap-Assisted Tunneling in Ge pFET Junctions. Journal of the Electrochemical Society, 2011, 158, H955.	2.9	17
110	New concepts for integrated solid state detector electronics. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1988, 273, 625-629.	1.6	16
111	Filmâ€edgeâ€induced dislocation generation in silicon substrates. III. High voltage transmission electron microscopy observations and theoretical results for (1l„11) and (011) silicon substrates. Journal of Applied Physics, 1988, 63, 5703-5711.	2.5	16
112	Recent progress in the understanding of crystallographic defects in silicon. Journal of Crystal Growth, 1993, 126, 41-62.	1.5	16
113	Empirical model for the low-frequency noise of hot-carrier degraded submicron LDD MOSFETs. IEEE Electron Device Letters, 1997, 18, 480-482.	3.9	16
114	Influence of Tin Impurities on the Generation and Annealing of Thermal Oxygen Donors in Czochralski Silicon at 450Â°C. Journal of the Electrochemical Society, 2000, 147, 2727.	2.9	16
115	Short-channel effects in the Lorentzian noise induced by the EVB tunneling in partially-depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 747-758.	1.4	16
116	Electrically active defects in irradiated n-type Czochralski silicon doped with group IV impurities. Journal of Physics Condensed Matter, 2005, 17, S2255-S2266.	1.8	16
117	Radiation-induced defects in SiC-MESFETs after 2-MeV electron irradiation. Physica B: Condensed Matter, 2006, 376-377, 382-384.	2.7	16
118	Inherent density of point defects in thermal tensile strained (100)Siâ•SiO2 entities probed by electron spin resonance. Applied Physics Letters, 2006, 89, 152103.	3.3	16
119	Lifetime and leakage current considerations in metal-doped germanium. Journal of Materials Science: Materials in Electronics, 2007, 18, 799-804.	2.2	16
120	On the 1/f noise of triple-gate field-effect transistors with high-k gate dielectric. Applied Physics Letters, 2009, 95, 032101.	3.3	16
121	Study of electrically active lattice defects in Cf-252 and proton irradiated silicon diodes. IEEE Transactions on Nuclear Science, 1992, 39, 1747-1753.	2.0	15
122	p-n junction peripheral current analysis using gated diode measurements. Applied Physics Letters, 1998, 72, 3503-3505.	3.3	15
123	Improved extraction of the activation energy of the leakage current in silicon pâ€“n junction diodes. Applied Physics Letters, 2001, 78, 1997-1999.	3.3	15
124	Impact of Direct Plasma Hydrogenation on Thermal Donor Formation in n-Type CZ Silicon. Journal of the Electrochemical Society, 2005, 152, G16.	2.9	15
125	Analysis of the Leakage Current Origin in Thin Strain Relaxed Buffer Substrates. Journal of the Electrochemical Society, 2006, 153, G379.	2.9	15
126	Degradation of GaN LEDs by electron irradiation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 57-60.	3.5	15

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127	Kink-related noise overshoot in SOI n-MOSFETS operating at 4.2 K. Electronics Letters, 1992, 28, 577.	1.0	14
128	Random telegraph signals in siliconâ€onâ€insulator metalâ€oxideâ€semiconductor transistors. Journal of Applied Physics, 1994, 75, 3647-3653.	2.5	14
129	The cryogenic operation of partially depleted silicon-on-insulator inverters. IEEE Transactions on Electron Devices, 1995, 42, 1100-1105.	3.0	14
130	Impact of the free electron distribution on the random telegraph signal capture kinetics in submicron n-metalâ€“oxideâ€“semiconductor field-effect transistors. Applied Physics Letters, 1998, 73, 2444-2446.	3.3	14
131	pâ€n Junction Diagnostics to Determine Surface and Bulk Generation/Recombination Properties of Silicon Substrates. Journal of the Electrochemical Society, 1999, 146, 1151-1157.	2.9	14
132	Impact of the divacancy (?) on the generation-recombination properties of 10 MeV proton irradiated Float-Zone silicon diodes. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2000, 439, 310-318.	1.6	14
133	Peripheral current analysis of silicon pâ€“n junction and gated diodes. Journal of Applied Physics, 2000, 88, 6506-6514.	2.5	14
134	Impact of the high vertical electric field on low-frequency noise in thin-gate oxide MOSFETs. IEEE Transactions on Electron Devices, 2003, 50, 2520-2527.	3.0	14
135	Excess Lorentzian Noise in Partially Depleted SOI nMOSFETs Induced by an Accumulation Back-Gate Bias. IEEE Electron Device Letters, 2004, 25, 433-435.	3.9	14
136	Electrical stresses on ultra-thin gate oxide SOI MOSFETs after irradiation. IEEE Transactions on Nuclear Science, 2005, 52, 2252-2258.	2.0	14
137	Defect engineering aspects of advanced Ge process modules. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 49-55.	3.5	14
138	Low-frequency noise assessment of the silicon passivation of Ge pMOSFETs. Thin Solid Films, 2010, 518, 2493-2496.	1.8	14
139	Low-Frequency Noise Studies on Fully Depleted UTBOX Silicon-on-Insulator nMOSFETs: Challenges and Opportunities. ECS Journal of Solid State Science and Technology, 2013, 2, Q205-Q210.	1.8	14
140	Combined low-frequency noise and random telegraph signal analysis of silicon MOSFET's. Applied Surface Science, 1993, 63, 285-290.	6.1	13
141	Substrate bias effect on the random telegraph signal parameters in submicrometer siliconpâ€“metalâ€“oxideâ€“semiconductor transistors. Journal of Applied Physics, 1995, 77, 910-914.	2.5	13
142	Flicker noise in deep submicron nMOS transistors. Solid-State Electronics, 2000, 44, 1239-1245.	1.4	13
143	Impact of a high electric field on the extraction of the generation lifetime from the reverse generation current component of shallow n/sup +/-p-well diodes. IEEE Transactions on Electron Devices, 2001, 48, 2445-2446.	3.0	13
144	DLTS and PL studies of proton radiation defects in tin-doped FZ silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 19-23.	1.4	13

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145	Extraction of the carrier generation and recombination lifetime from the forward characteristics of advanced diodes. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 189-192.	3.5	13
146	Impact of the gate-electrode/dielectric interface on the low-frequency noise of thin gate oxide n-channel metal-oxide-semiconductor field-effect transistors. Solid-State Electronics, 2007, 51, 627-632.	1.4	13
147	Electrical and Structural Properties of Oxygen-Precipitation Induced Extended Defects in Silicon. Journal De Physique III, 1997, 7, 1469-1486.	0.3	13
148	The low-frequency noise overshoot in partially depleted n-channel silicon-on-insulator twin-MOST's. IEEE Transactions on Electron Devices, 1994, 41, 1972-1976.	3.0	12
149	The response of Si p - n junction diodes to proton irradiation. Semiconductor Science and Technology, 1996, 11, 1434-1442.	2.0	12
150	Impact of CMOS processing steps on the drain current kink of NMOSFETs at liquid helium temperature. IEEE Transactions on Electron Devices, 2001, 48, 1207-1215.	3.0	12
151	Improved extraction of carrier concentration and depletion width from capacitanceâ€“voltage characteristics of silicon n+â€“p-well junction diodes. Applied Physics Letters, 2002, 80, 1192-1194.	3.3	12
152	Impact of gate tunneling floating-body charging on drain current transients of 0.10 Î¼m-CMOS partially depleted SOI MOSFETs. Solid-State Electronics, 2004, 48, 1211-1221.	1.4	12
153	Defect analysis of strained silicon on thin strain-relaxed buffer layers for high mobility transistors. Journal of Physics Condensed Matter, 2005, 17, S2197-S2210.	1.8	12
154	Effect of Nitridation on Low-Frequency (1/f) Noise in n- and p-MOSFETS with HFO[sub 2] Gate Dielectrics. Journal of the Electrochemical Society, 2006, 153, G819.	2.9	12
155	A deep-level transient spectroscopy study of Co- and Ni-germanided n-type germanium. Materials Science in Semiconductor Processing, 2006, 9, 554-558.	4.0	12
156	Leakage Current Control in Recessed SiGe Source/Drain Junctions. Journal of the Electrochemical Society, 2007, 154, H814.	2.9	12
157	The low-frequency noise behaviour of graded-channel SOI nMOSFETs. Solid-State Electronics, 2007, 51, 260-267.	1.4	12
158	Effect of rotation, gate-dielectric and SEG on the noise behavior of advanced SOI MuGFETs. Solid-State Electronics, 2010, 54, 178-184.	1.4	12
159	Extended-Defect Aspects of Ge-on-Si Materials and Devices. Journal of the Electrochemical Society, 2010, 157, R1.	2.9	12
160	Pulsed laser-induced transient currents in bulk and silicon-on-insulator FinFETs. , 2011, , .		12
161	In depth static and low-frequency noise characterization of n-channel FinFETs on SOI substrates at cryogenic temperature. Solid-State Electronics, 2014, 98, 12-19.	1.4	12
162	Low-Frequency Noise Assessment of Work Function Engineering Cap Layers in High-k Gate Stacks. ECS Journal of Solid State Science and Technology, 2019, 8, N25-N31.	1.8	12

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163	Analytical model for the current-voltage characteristics of a silicon resistor at liquid helium temperatures. Cryogenics, 1990, 30, 1152-1159.	1.7	11
164	Investigation of drain current RTS noise in small area silicon MOS transistors. Microelectronic Engineering, 1991, 15, 547-550.	2.4	11
165	A study of the kinkâ€related excess lowâ€frequency noise in siliconâ€onâ€insulatornâ€metalâ€oxideâ€semiconductor transistors operated at liquid helium temperatures. Journal of Applied Physics, 1992, 72, 1416-1422.	2.5	11
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